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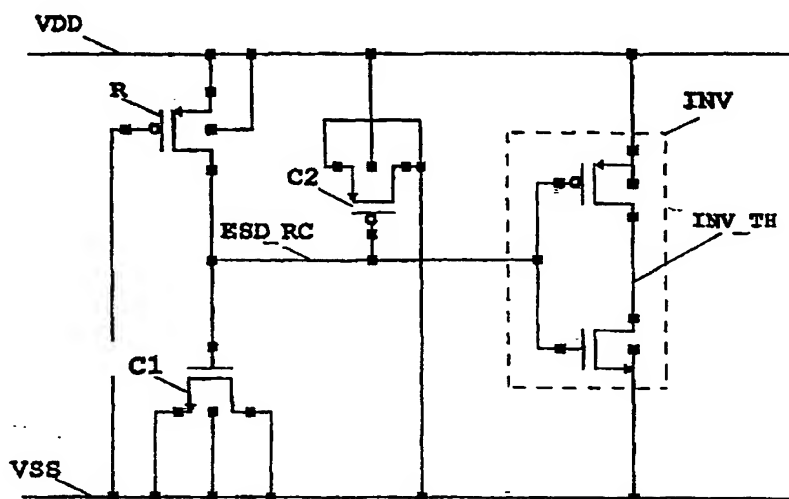
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(54) Title: CIRCUIT FOR ELECTROSTATIC DISCHARGE PROTECTION



(57) Abstract: A circuit providing protection against electrostatic discharge (ESD) for internal elements of an Integrated Circuit (IC) is connected to a power rail (VDD) and a ground rail (VSS) and to an inverter (INV) of a clamp preamplifier. The protection circuit comprises a PMOSFET resistor (R) with a gate connected to said ground rail (VSS), a drain connected to said inverter's (INV) input node (ESD_RC), a source and a bulk connected to said power rail (VDD). The circuit also comprises an NMOSFET capacitor (C1) with a gate connected to said inverter's (INV) input node (ESD_RC), a drain, a source and a bulk connected to said ground rail (VSS), and a PMOSFET connector (C2) with a gate connected to said inverter's (INV) input node (ESD_RC), a drain, a source connected to said ground rail (VSS) and a bulk connected to said power rail (VDD).

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